



BTA16-xxxSW BTB16-xxxSW

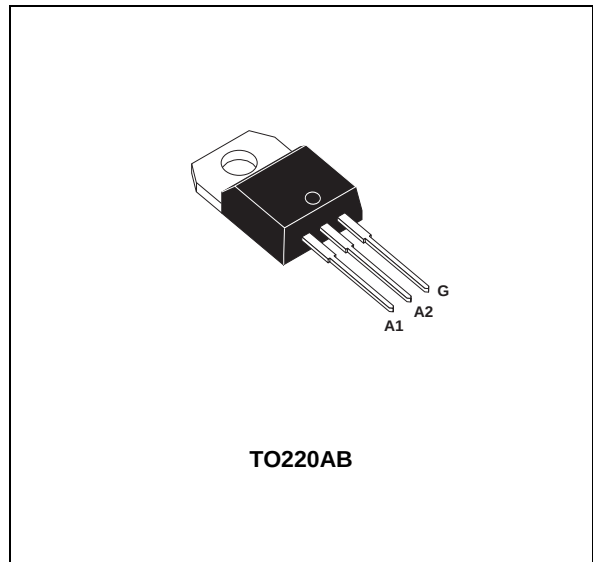
HIGH PERFORMANCE LOGIC LEVEL TRIACS

FEATURES

- $I_{T(RMS)} = 16A$
- LOGIC LEVEL TRIGGERING: $I_{GT} \leq 10mA$
- HIGH SURGE CAPABILITY

DESCRIPTION

The BTA/BTB16-xxxSW triacs are using a high performance glass passivated technology. These triacs are designed for applications requiring high inrush current performances such as fridge motor control, magnetron supply of microwave ovens, halogen range cookers, etc...). The high gate sensitivity makes them perfectly suited for direct gate triggering by microcontrollers and other logic circuits.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	BTA	Tc = 85 °C	16	A
		BTB	Tc = 105 °C		
I_{TSM}	Non repetitive surge peak on-state current (Tj initial = 25°C)		tp = 8.3 ms	170	A
			tp = 10 ms	160	
I^2t	I^2t value for fusing		tp = 10 ms	128	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : IG = 20mA , tr ≤ 100ns		Repetitive F = 100 Hz	50	A/μs
Tstg Tj	Storage and operating junction temperature range			- 40 to + 150 - 40 to + 125	°C °C
TI	Maximum lead temperature for soldering during 10s at 4.5mm from case			260	°C

Symbol	Parameter	BTA / BTB16-xxxSW		Unit
		600	700	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125\text{ °C}$	600	700	V

BTA/BTB16-xxxSW

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	2.8	°C/W
		BTB	1.6	
Rth (j-c) AC	Junction to case for AC 360° conduction angle (F= 50 Hz)	BTA	2.1	°C/W
		BTB	1.2	

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 1W$ $P_{GM} = 10W$ ($t_p = 20 \mu s$) $I_{GM} = 4A$ ($t_p = 20 \mu s$).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		BTA/BTB16-xxxSW	Unit
					Value	
I_{GT}	$V_D=12V$ (DC) $R_L=33\Omega$	$T_j=25^\circ C$	I-II-III	MAX	10	mA
V_{GT}	$V_D=12V$ (DC) $R_L=33\Omega$	$T_j=25^\circ C$	I-II-III	MAX	1.3	V
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3k\Omega$	$T_j=125^\circ C$	I-II-III	MIN	0.2	V
I_L	$I_G=1.2 I_{GT}$	$T_j=25^\circ C$	I-III	MAX	30	mA
			II	MAX	40	
I_H *	$I_T=100mA$ gate open	$T_j=25^\circ C$		MAX	15	mA
V_{TM} *	$I_{TM}=22.5A$ $t_p=380\mu s$	$T_j=25^\circ C$		MAX	1.5	V
I_{DRM} I_{RRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j=25^\circ C$		MAX	5	μA
		$T_j=125^\circ C$		MAX	2	mA
dV/dt *	$V_D=67\%V_{DRM}$ gate open	$T_j=125^\circ C$		MIN	20	V/ μs
$(dI/dt)_c$ *	$(dV/dt)_c = 0.1V/\mu s$	$T_j=125^\circ C$		MIN	3.5	A/ms
	Without snubber	$T_j=125^\circ C$		MIN	1	

* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

BTB 16 - 600 S W					
TRIAC : BTB : UNINSULATED BTA : INSULATED		CURRENT	VOLTAGE	SENSITIVITY	3 QUADRANTS

Fig.1 : Maximum power dissipation versus RMS on-state current (resistive load).

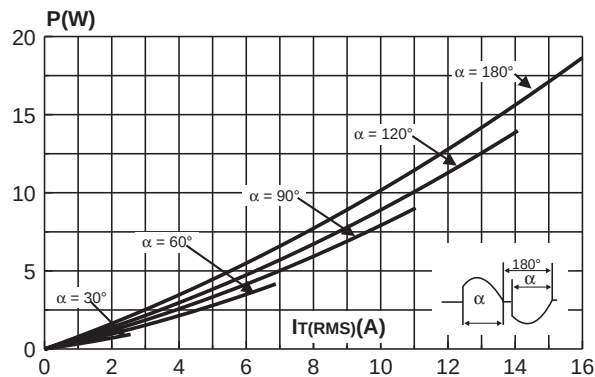


Fig.2-1 : Correlation between maximum power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances (BTA).

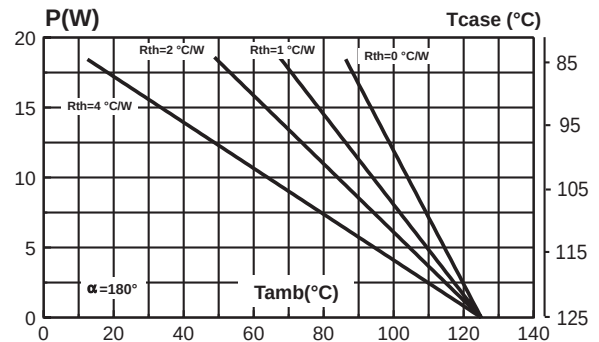


Fig.2-2 : Correlation between maximum power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

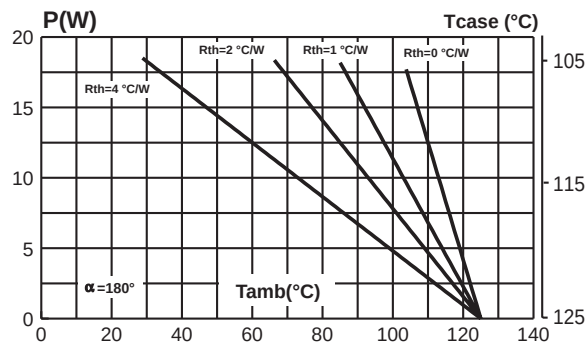


Fig.3 : RMS on-state current versus case temperature.

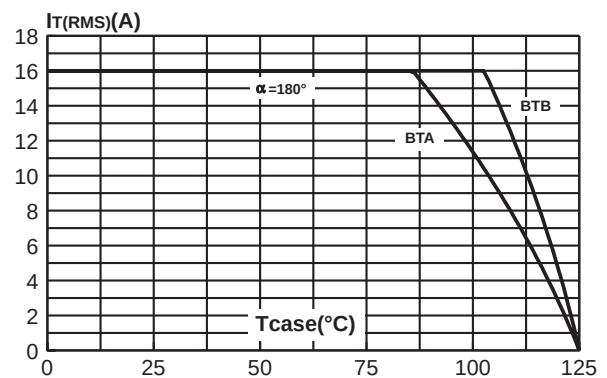


Fig.4 : Relative variation of thermal impedance versus pulse duration.

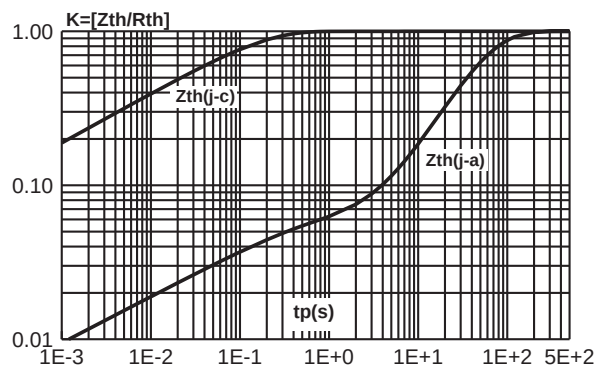


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature (typical values).

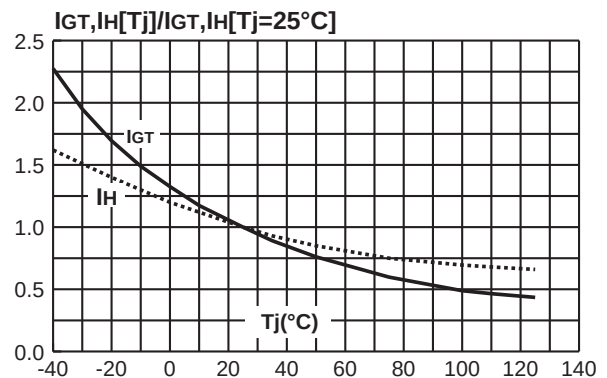


Fig.6 : Non Repetitive surge peak on-state current versus number of cycles.

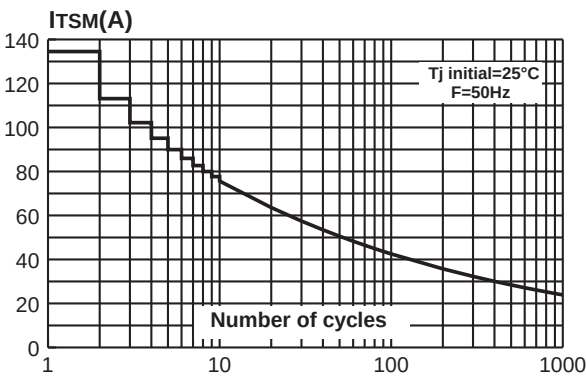


Fig 7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10$ ms, and corresponding value of I^2t .

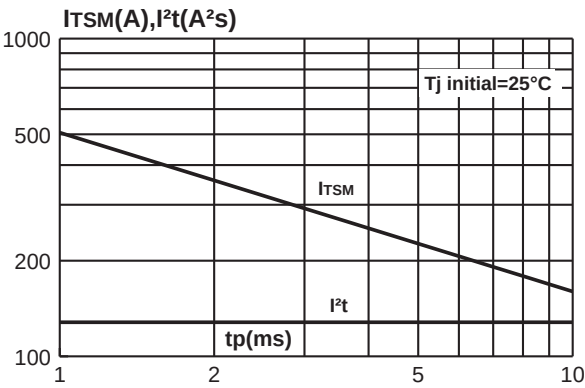
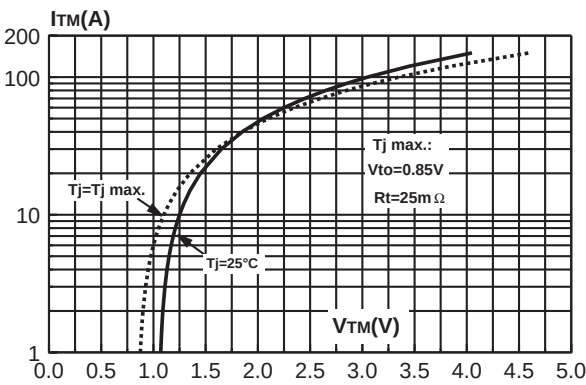
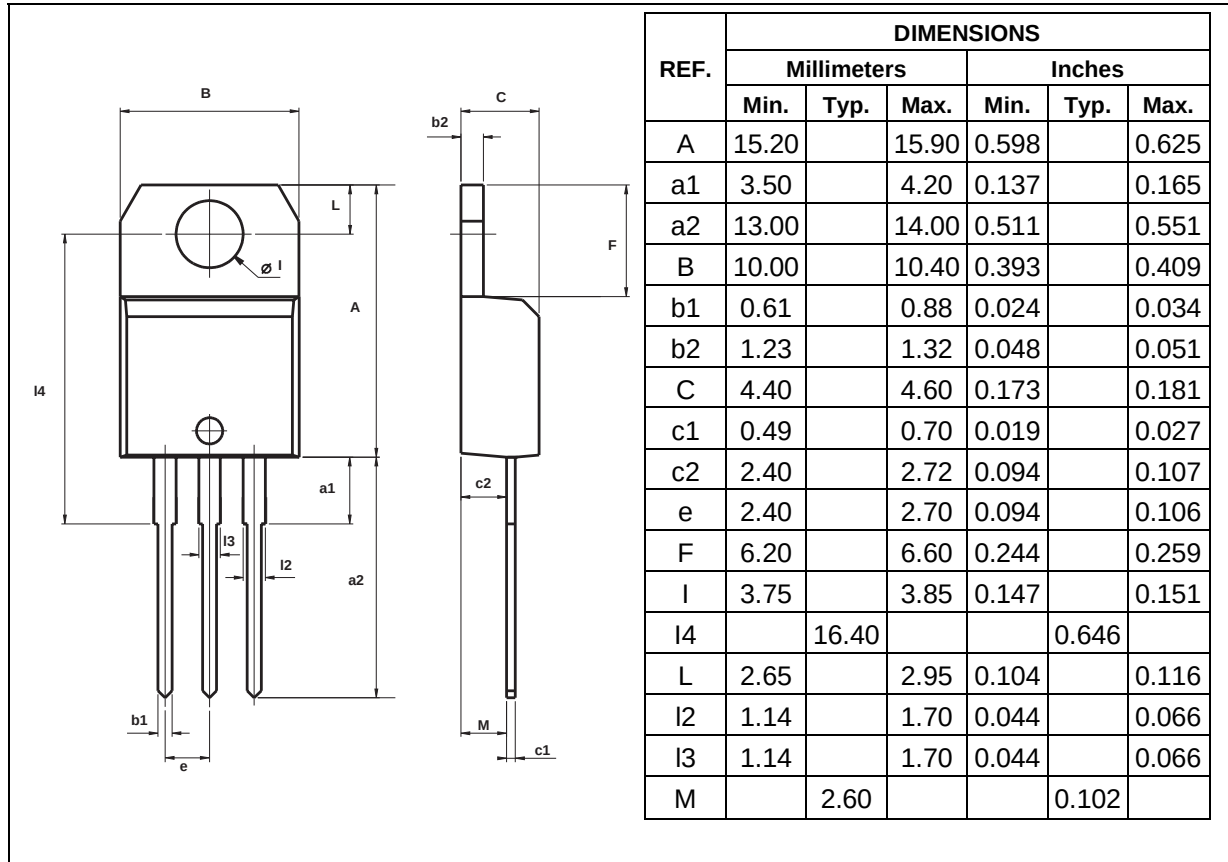


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA
 TO220AB Plastic

MARKING

Type	Marking
BTA16-600SW	BTA16 600SW
BTA16-700SW	BTA16 700SW
BTB16-600SW	BTB16 600SW
BTB16-700SW	BTB16 700SW

Weight : 2.1g

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